

## 3M™ Static Shielding Bags Product Selection Guide

Product	Technology	Benefit	Application
<i>Metal-In Shielding Bag</i>			
<b>SCC 1000</b>	Metal-In Static Shielding Bag	Four-layer construction. Polyester dielectric and metal layer provide Faraday effect shielding of ESD and fields. Tribocharging is minimized by the specially processed polyethylene. Lot coded for QC traceability.	Transparent, metallized static shielding bag provides a static safe environment for sensitive electronic devices.
<i>Metal-Out Shielding Bag</i>			
<b>SCC 1500</b>	Metal-Out Static Shielding Bag	Provides low charge retention and rapid static decay. These bags are approved by major computer, electronics, and disk drive manufacturers for use worldwide. Lot coded for QC traceability.	Best protection from ESD through low charge retention and rapid static decay.
<i>ZipTop Reclosable Bags</i>			
<b>SCC 1000</b> <b>SCC 1300</b> <b>SCC 1500</b> <b>3M 2110R</b>	Reclosable ZipTop Static Shielding Bag	ZipTop feature makes the bag easy to open and close. Lot coded for QC traceability.	Easy to open and close. Transparent, metallized static shielding bags provide a static safe environment for sensitive electronic devices.
<i>Puncture Resistant Shielding Bags</i>			
<b>SCC 1300</b>	Puncture Resistant Metal-In Static Shielding Bag	High puncture resistance provides a long life and reduces tears. Four-layer construction. Polyester dielectric and metal layer provide Faraday effect shielding of ESD and fields. Lot coded for QC traceability.	For tubes and heavy items. Transparent, metallized static shielding bag provides a static safe environment for sensitive electronic devices.
<b>3M 2100R</b>	Puncture Resistant Metal-Out Static Shielding Bag	High puncture resistance provides long life and reduces tears. Metallized bag structure provides a static safe environment for sensitive electronic devices. Provides low charge retention and rapid static decay. Lot coded for QC traceability.	For tubes and heavy items. Best protection from ESD through low charge retention and rapid static decay.